

Supplementary Information

Fluorine-enhanced Room-temperature Luminescence of Er-doped Crystalline Silicon

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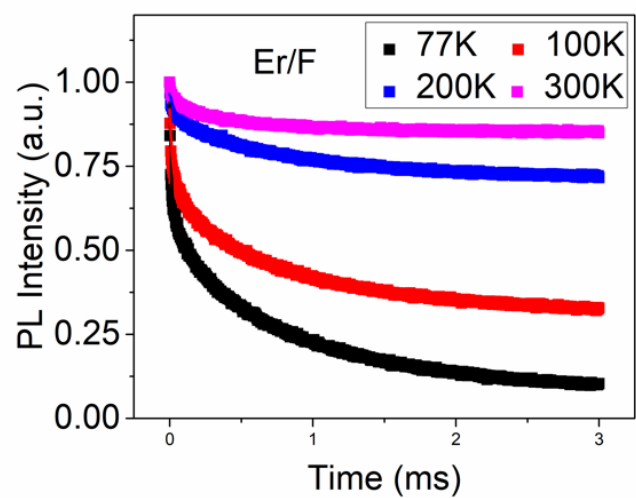
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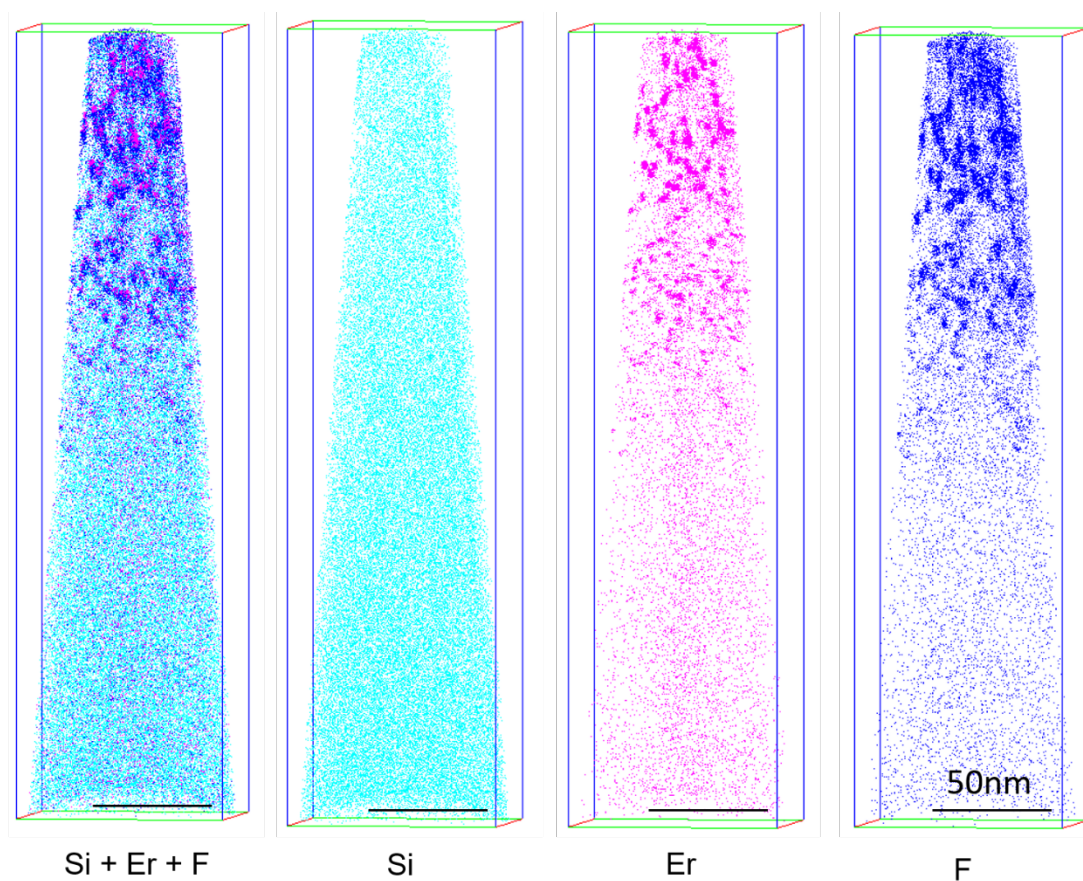
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Supplementary Figure 1. Transient decay traces at different temperatures for the Er/F: Si sample.



Supplementary Figure 2. Three-dimensional reconstruction volume of Er and F atoms of RTA-treated Er/F: Si sample obtained by APT techniques.